

ABSTRACT OF THE DISCLOSURE

A thin film semiconductor device formed as integrated circuits on an insulating substrate with bottom gate type thin film transistors stacked with gate electrodes, a gate insulating film and a semiconductor thin film in the order from below upward. The gate electrodes comprise metallic materials with thickness less than 100nm. The gate insulating film has a thickness thicker than the gate electrodes. The semiconductor thin film comprises polycrystalline silicon crystallized by a laser beam. By reducing thickness of metallic gate electrodes, thermal capacity becomes small and difference in thermal condition on the metallic gate electrodes and on the insulating substrate made of glass or the like becomes small. This invention relates to the task of uiforming and optimizing recrystallization by a laser anneal treatment provided for the semiconductor thin film which works as an active layer of the bottom gate type thin film transistors.